

## 3.3 Volt CMOS DUAL ASYNCHRONOUS FIFO DUAL 512 x 9, DUAL 1,024 x 9 DUAL 2,048 x 9, DUAL 4,096 X 9 DUAL 8,192 X 9

#### IDT72V81 IDT72V82 IDT72V83 IDT72V84 IDT72V85

LEAD FINISH (SnPb) ARE IN EOL PROCESS - LAST TIME BUY EXPIRES JUNE 15, 2018

## FEATURES:

- The IDT72V81 is equivalent to two IDT72V01 512 x 9 FIFOs
- The IDT72V82 is equivalent to two IDT72V02 1,024 x 9 FIFOs
- The IDT72V83 is equivalent to two IDT72V03 2,048 x 9 FIFOs
- The IDT72V84 is equivalent to two IDT72V04 4,096 x 9 FIFOs
- The IDT72V85 is equivalent to two IDT72V05 8,192 x 9 FIFOs
- Low power consumption
  - Active: 330 mW (max.)
  - Power-down: 18 mW (max.)
- Ultra high speed—15 ns access time
- Asynchronous and simultaneous read and write
- Offers optimal combination of data capacity, small foot print and functional flexibility
- Ideal for bidirectional, width expansion, depth expansion, busmatching, and data sorting applications
- Status Flags: Empty, Half-Full, Full
- Auto-retransmit capability
- High-performance CMOS<sup>™</sup> technology
- Space-saving TSSOP package
- Industrial temperature range (-40°C to +85°C) is available
- Green parts available, see ordering information

FUNCTIONAL BLOCK DIAGRAM

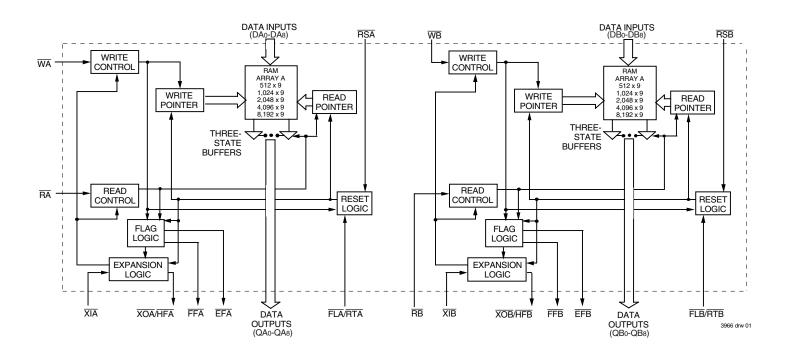
## DESCRIPTION:

The IDT72V81/72V82/72V83/72V84/72V85 are dual-FIFO memories that load and empty data on a first-in/first-out basis. These devices are functional and compatible to two IDT72V01/72V02/72V03/72V04/72V05 FIFOs in a single package with all associated control, data, and flag lines assigned to separate pins. The devices use Full and Empty flags to prevent data overflow and underflow and expansion logic to allow for unlimited expansion capability in both word size and depth.

The reads and writes are internally sequential through the use of ring pointers, with no address information required to load and unload data. Data is toggled in and out of the devices through the use of the Write  $(\overline{W})$  and Read  $(\overline{R})$  pins.

The devices utilize a 9-bit wide data array to allow for control and parity bits at the user's option. This feature is especially useful in data communications applications where it is necessary to use a parity bit for transmission/reception error checking. It also features a Retransmit ( $\overline{RT}$ ) capability that allows for reset of the read pointer to its initial position when  $\overline{RT}$  is pulsed low to allow for retransmission from the beginning of data. A Half-Full Flag is available in the single device mode and width expansion modes.

These FIFOs are fabricated using high-speed CMOS technology. They are designed for those applications requiring asynchronous and simultaneous read/writes in multiprocessing and rate buffer applications.



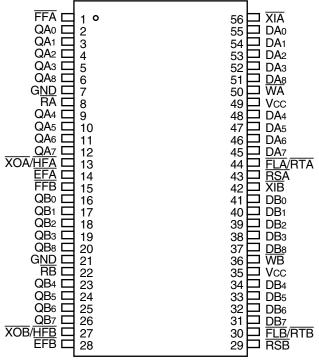
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### NOVEMBER 2017

## IDT72V81/72V82/72V83/72V84/72V853.3V CMOS DUAL ASYNCHRONOUS FIFO 512 x 9, 1024 x 9, 2048 x 9, 4096 x 9, 8192 x 9

## PIN CONFIGURATION



3966 drw 02

TSSOP (SO56-2, order code: PA) TOP VIEW

## DC ELECTRICAL CHARACTERISTICS<sup>(1)</sup>

(Commercial: VCC =  $3.3V \pm 0.3V$ , TA = 0°C to +70°C; Industrial: VCC =  $3.3V \pm 0.3V$ , TA =  $-40^{\circ}$ C to  $\pm 85^{\circ}$ C)

Symbol	Rating	Com'l & Ind'l	Unit
Vterm	Terminal Voltage with Respect to GND	-0.5 to +7.0	V
Tstg	Storage Temperature	–55 to +125	°C
Ιουτ	DC Output Current	-50 to +50	mA

NOTE:

 Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

# RECOMMENDED DC OPERATING CONDITIONS

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	3.0	3.3	3.6	V
GND	Supply Voltage	0	0	0	V
VIH <sup>(1)</sup>	Input High Voltage	2.0	—	Vcc+0.5	V
VIL <sup>(2)</sup>	Input Low Voltage	—	—	0.8	V
TA	Operating Temperature Commercial	0	—	70	°C
TA	Operating Temperature Industrial	-40	—	85	°C

NOTES:

1. For  $\overline{RT/RS/XI}$  input, VIH = 2.6V (commercial and industrial).

2. 1.5V undershoots are allowed for 10ns once per cycle

#### CAPACITANCE (TA = +25°C, f = 1.0 MHz)

Symbol	Parameter <sup>(1)</sup>	Condition	Max.	Unit
CIN	Input Capacitance	VIN = 0V	8	рF
Соит	Output Capacitance	Vout = 0V	8	pF

#### NOTE:

1. Characterized values, not currently tested.

		Commercial ta = 15, 20 ns		Indu tA = 2		
Symbol	Parameter	Min.	Min. Max. Min. Max.		Unit	
ILI <sup>(1)</sup>	Input Leakage Current (Any Input)	-1	1	-1	1	μA
Ilo <sup>(2)</sup>	Output Leakage Current	-10	10	-10	10	μA
Vон	Output Logic "1" Voltage IOH = -2mA	2.4	-	2.4	_	V
Vol	Output Logic "0" Voltage IoL = 8mA	—	0.4	—	0.4	V
ICC1 <sup>(3,4)</sup>	Active Power Supply Current (both FIFOs)	—	100	_	120	mA
ICC2 <sup>(3,5)</sup>	Standby Current ( $\overline{R}=\overline{W}=\overline{RS}=\overline{FL}/\overline{RT}=VIH$ )	—	5	—	5	mA

NOTES:

- 1. Measurements with  $0.4 \le V_{IN} \le V_{CC}$ .
- 2.  $\overline{R} \ge V_{IH}$ ,  $0.4 \le V_{OUT} \le V_{CC}$ .

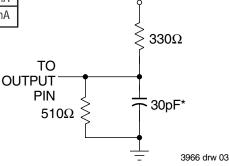
Tested with outputs open (IOUT = 0).

4. Tested at f = 20 MHz.

5. All Inputs = Vcc - 0.2V or GND + 0.2V.

## AC TEST CONDITIONS

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	5ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	See Figure 1
Input Timing Reference Levels Output Reference Levels	1.5V 1.5V



3.3V

or equivalent circuit **Figure 1. Output Load** \*Includes scope and jib capacitances.

## AC ELECTRICAL CHARACTERISTICS<sup>(1)</sup>

(Commercial: Vcc = 3.3V±0.3V, TA = 0°C to +70°C; Industrial: Vcc = 3.3V±0.3V, TA = -40°C to +85°C)

		Com	mercial	Commercial	& Industrial	
Symbol		IDT72\ IDT72\ IDT72\ IDT72\ IDT72\ IDT72\	IDT72V81L20 IDT72V82L20 IDT72V83L20 IDT72V84L20 IDT72V85L20			
	Parameter	Min.	Max.	Min.	Max.	Unit
ts	Shift Frequency	_	40	—	33.3	MHz
trc	Read Cycle Time	25	_	30	_	ns
tA	Access Time	_	15	_	20	ns
trr	Read Recovery Time	10	_	10	_	ns
trpw	Read Pulse Width <sup>(2)</sup>	15	_	20	_	ns
trlz	Read Pulse Low to Data Bus at Low Z <sup>(3)</sup>	3	_	3	_	ns
twlz	Write Pulse High to Data Bus at Low $Z^{(3,4)}$	5	_	5	—	ns
tDV	Data Valid from Read Pulse High	5	_	5	_	ns
tRHZ	Read Pulse High to Data Bus at High Z <sup>(3)</sup>	_	15	—	15	ns
twc	Write Cycle Time	25	_	30	_	ns
twpw	Write Pulse Width <sup>(2)</sup>	15	_	20	_	ns
twr	Write Recovery Time	10	_	10	_	ns
tDS	Data Set-up Time	11	_	12	_	ns
tDH	Data Hold Time	0	_	0	_	ns
trsc	Reset Cycle Time	25	_	30		ns
trs	Reset Pulse Width <sup>(2)</sup>	15	_	20	_	ns
trss	Reset Set-up Time <sup>(3)</sup>	15	_	20	_	ns
trsr	Reset Recovery Time	10	_	10	_	ns
<b>I</b> RTC	RetransmitCycleTime	25	_	30	_	ns
trt	Retransmit Pulse Width <sup>(2)</sup>	15	_	20	_	ns
trts	RetransmitSet-upTime <sup>(3)</sup>	15	_	20	_	ns
<b>İ</b> RTR	Retransmit Recovery Time	10	_	10	_	ns
tefl	Reset to Empty Flag Low		25	_	30	ns
HFH,FFH	Reset to Half-Full and Full Flag High	_	25	_	30	ns
<b>t</b> RTF	Retransmit Low to Flags Valid	_	25	_	30	ns
IREF	Read Low to Empty Flag Low	—	15	—	20	ns
İRFF	Read High to Full Flag High	_	15	_	20	ns
RPE	Read Pulse Width after EF High	15	_	20	_	ns
WEF	Write High to Empty Flag High	_	15	_	20	ns
İWFF	Write Low to Full Flag Low		15	_	20	ns
WHF	Write Low to Half-Full Flag Low	_	25	_	30	ns
RHF	Read High to Half-Full Flag High	_	25	_	30	ns
WPF	Write Pulse Width after FF High	15	_	20	_	ns
XOL	Read/Write to XO Low	_	15	_	20	ns
ХОН	Read/Write to XO High	_	15	_	20	ns
İXI	XIPulse Width <sup>(2)</sup>	15	_	20	_	ns
XIR	XI Recovery Time	10	_	10	_	ns
txis	XI Set-up Time	10	_	10	_	ns

NOTES:

1. Timings referenced as in AC Test Conditions.

2. Pulse widths less than minimum value are not allowed.

3. Values guaranteed by design, not currently tested.

4. Only applies to read data flow-through mode.

## SIGNAL DESCRIPTIONS

## **INPUTS:**

DATA IN (Do – D8)

Data inputs for 9-bit wide data.

## CONTROLS:

## RESET (RS)

Reset is accomplished whenever the Reset ( $\overline{RS}$ ) input is taken to a low state. During reset, both internal read and write pointers are set to the first location. A reset is required after power up before a write operation can take place. Both the Read Enable ( $\overline{R}$ ) and Write Enable ( $\overline{W}$ ) inputs must be in the high state during the window shown in Figure 2, (i.e., tRSS before the rising edge of  $\overline{RS}$ ) and should not change until tRSR after the rising edge of  $\overline{RS}$ . Half-Full Flag ( $\overline{HF}$ ) will be reset to high after Reset ( $\overline{RS}$ ).

#### WRITE ENABLE (W)

A write cycle is initiated on the falling edge of this input if the Full Flag ( $\overline{FF}$ ) is not set. Data set-up and hold times must be adhered to with respect to the rising edge of the Write Enable ( $\overline{W}$ ). Data is stored in the RAM array sequentially and independently of any on-going read operation.

After half of the memory is filled and at the falling edge of the next write operation, the Half-Full Flag ( $\overline{HF}$ ) will be set to low and will remain set until the difference between the write pointer and read pointer is less than or equal to one half of the total memory of the device. The Half-Full Flag ( $\overline{HF}$ ) is then reset by the rising edge of the read operation.

To prevent data overflow, the Full Flag ( $\overline{FF}$ ) will go low, inhibiting further write operations. Upon the completion of a valid read operation, the Full Flag ( $\overline{FF}$ ) will go high after tRFF, allowing a valid write to begin. When the FIFO is full, the internal write pointer is blocked from  $\overline{W}$ , so external changes in  $\overline{W}$  will not affect the FIFO when it is full.

#### READ ENABLE (R)

A read cycle is initiated on the falling edge of the Read Enable ( $\overline{R}$ ) provided the Empty Flag ( $\overline{EF}$ ) is not set. The data is accessed on a First-In/First-Out basis, independent of any ongoing write operations. After Read Enable ( $\overline{R}$ ) goes high, the Data Outputs ( $Qo - Q_8$ ) will return to a high impedance condition until the next Read operation. When all data has been read from the FIFO, the Empty Flag ( $\overline{EF}$ ) will go low, allowing the "final" read cycle but inhibiting further read operations with the data outputs remaining in a high impedance state. Once a valid write operation has been accomplished, the Empty Flag ( $\overline{EF}$ ) will go high after tWEF and a valid Read can then begin. When the FIFO is empty, the internal read pointer is blocked from  $\overline{R}$  so external changes in  $\overline{R}$  will not affect the FIFO when it is empty.

### FIRST LOAD/RETRANSMIT (FL/RT)

This is a dual-purpose input. In the Depth Expansion Mode, this pin is grounded to indicate that it is the first loaded (see Operating Modes). In the

Single Device Mode, this pin acts as the retransmit input. The Single Device Mode is initiated by grounding the Expansion In  $(\overline{XI})$ .

The IDT72V81/72V82/72V83/72V84/72V85 can be made to retransmit data when the Retransmit Enable control ( $\overline{RT}$ ) input is pulsed low. A retransmit operation will set the internal read pointer to the first location and will not affect the write pointer. Read Enable ( $\overline{R}$ ) and Write Enable ( $\overline{W}$ ) must be in the high state during retransmit for the IDT72V81/72V82/72V83/72V84/72V85 respectively. This feature is useful when less than 512/1,024/2,048/4,096/8,192 writes are performed between resets. The retransmit feature is not compatible with the Depth Expansion Mode and will affect the Half-Full Flag ( $\overline{HF}$ ), depending on the relative locations of the read and write pointers.

#### EXPANSION IN (XI)

This input is a dual-purpose pin. Expansion In  $(\overline{XI})$  is grounded to indicate an operation in the single device mode. Expansion In  $(\overline{XI})$  is connected to Expansion Out  $(\overline{XO})$  of the previous device in the Depth Expansion or Daisy Chain Mode.

## OUTPUTS: FULL FLAG (FF)

The Full Flag ( $\overline{FF}$ ) will go low, inhibiting further write operation, when the write pointer is one location less than the read pointer, indicating that the device is full. If the read pointer is not moved after Reset ( $\overline{RS}$ ), the Full-Flag ( $\overline{FF}$ ) will go low after 512 writes for the IDT72V81, 1,024 writes for the IDT72V82, 2,048 writes for the IDT72V83, 4,096 writes for the IDT72V84 and 8,192 writes for the IDT72V85.

## EMPTY FLAG (EF)

The Empty Flag ( $\overline{\text{EF}}$ ) will go low, inhibiting further read operations, when the read pointer is equal to the write pointer, indicating that the device is empty.

#### EXPANSION OUT/HALF-FULL FLAG (XO/HF)

This is a dual-purpose output. In the single device mode, when Expansion In  $(\overline{XI})$  is grounded, this output acts as an indication of a half-full memory.

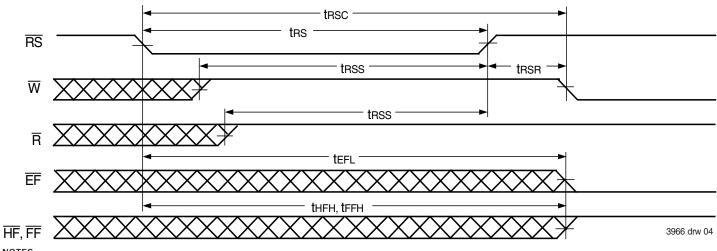
After half of the memory is filled and at the falling edge of the next write operation, the Half-Full Flag ( $\overline{HF}$ ) will be set low and will remain set until the difference between the write pointer and read pointer is less than or equal to one half of the total memory of the device. The Half-Full Flag ( $\overline{HF}$ ) is then reset by using rising edge of the read operation.

In the Depth Expansion Mode, Expansion In  $(\overline{XI})$  is connected to Expansion Out  $(\overline{XO})$  of the previous device in the Daisy Chain by providing a pulse to the next device when the previous device reaches the last location of memory.

#### DATA OUTPUTS (Q0 - Q8)

Data outputs for 9-bit wide data. This data is in a high impedance condition whenever Read  $(\overline{R})$  is in a high state.

#### IDT72V81/72V82/72V83/72V84/72V853.3V CMOS DUAL ASYNCHRONOUS FIFO 512 x 9, 1024 x 9, 2048 x 9, 4096 x 9, 8192 x 9



#### NOTES:

1. EF, FF, HF may change status during Reset, but flags will be valid at trsc. 2.  $\overline{W}$  and  $\overline{R} = V_{H}$  around the rising edge of  $\overline{RS}$ .

Figure 2. Reset

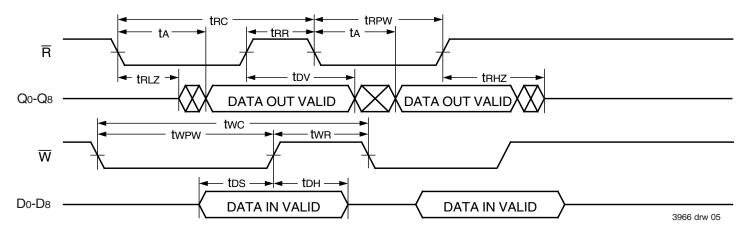


Figure 3. Asynchronous Write and Read Operation

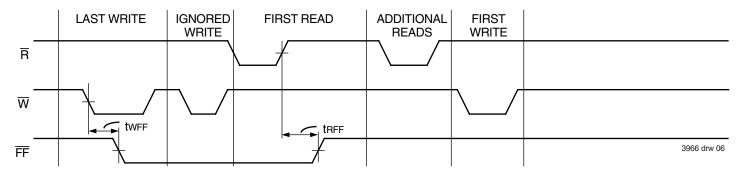


Figure 4. Full Flag From Last Write to First Read



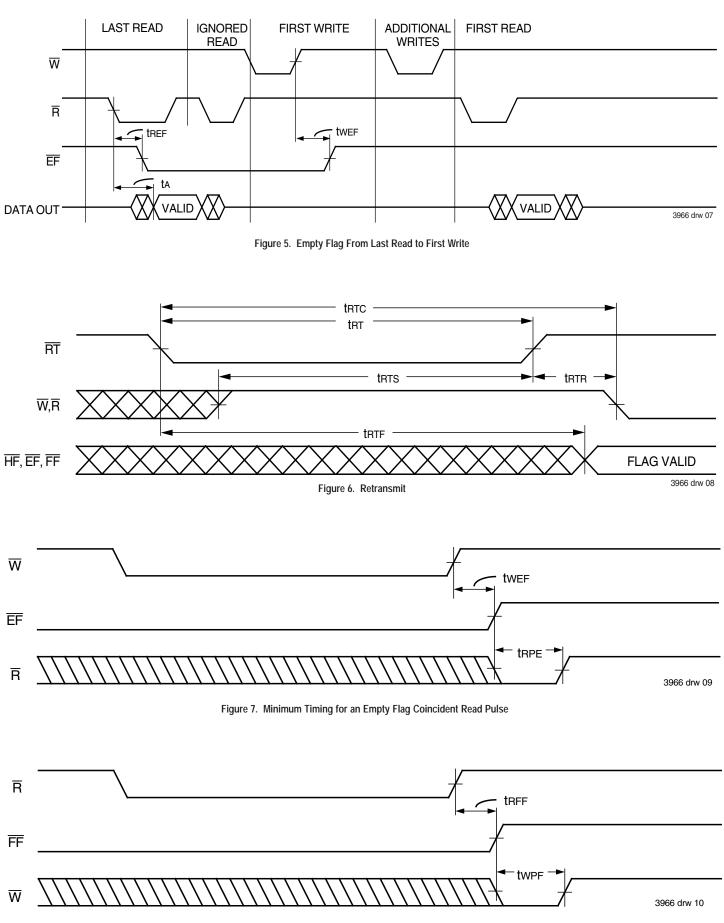
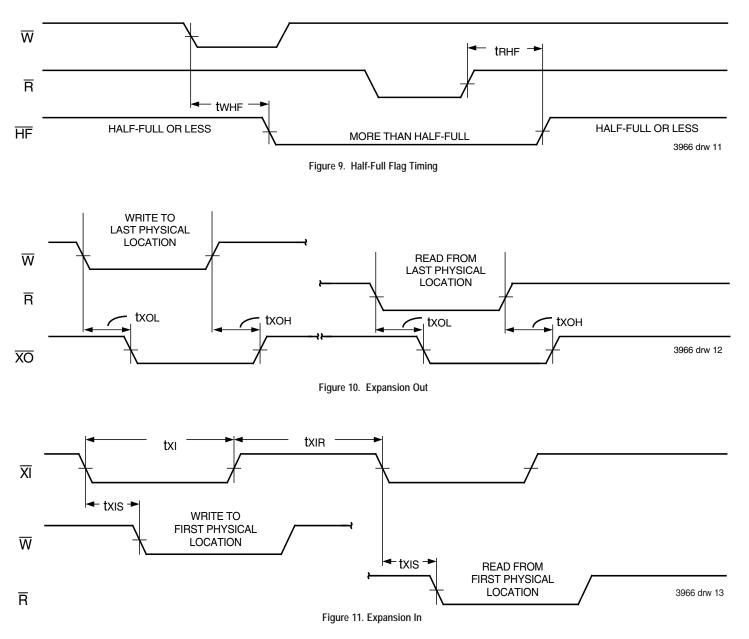


Figure 8. Minimum Timing for an Full Flag Coincident Write Pulse

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## IDT72V81/72V82/72V83/72V84/72V853.3V CMOS DUAL ASYNCHRONOUS FIFO 512 x 9, 1024 x 9, 2048 x 9, 4096 x 9, 8192 x 9



## OPERATING MODES:

Care must be taken to assure that the appropriate flag is monitored by each system (i.e.  $\overline{FF}$  is monitored on the device where  $\overline{W}$  is used;  $\overline{EF}$  is monitored on the device where  $\overline{R}$  is used).

#### Single Device Mode

A single IDT72V81/72V82/72V83/72V84/72V85 may be used when the application requirements are for 512/1,024/2,048/4,096/8,192 words or less. These FIFOs are in a Single Device Configuration when the Expansion In  $(\overline{XI})$  control input is grounded (see Figure 12).

#### **Depth Expansion**

These devices can easily be adapted to applications when the requirements are for greater than 512/1,024/2,048/4,096/8,192 words. Figure 14 demon-

strates a four-FIFO Depth Expansion using two IDT72V81/72V82/72V83/ 72V84/72V85s. Any depth can be attained by adding additional IDT72V81/ 72V82/72V83/72V84/72V85s. These FIFOs operate in the Depth Expansion mode when the following conditions are met:

- 1. The first FIFO must be designated by grounding the First Load (FL) control input.
- 2. All other FIFOs must have  $\overline{FL}$  in the high state.
- 3. The Expansion Out (XO) pin of each device must be tied to the Expansion In (XI) pin of the next device. See Figure 14.
- External logic is needed to generate a composite Full Flag (FF) and Empty Flag (EF). This requires the ORing of all EFs and ORing of all FFs (i.e. all must be set to generate the correct composite FF or EF). See Figure 14.
- 5. The Retransmit (RT) function and Half-Full Flag (HF) are not available in the Depth Expansion Mode.

## IDT72V81/72V82/72V83/72V84/72V853.3V CMOS DUAL ASYNCHRONOUS FIFO 512 x 9, 1024 x 9, 2048 x 9, 4096 x 9, 8192 x 9

#### COMMERCIAL AND INDUSTRIAL TEMPERATURE RANGES

## USAGE MODES:

#### Width Expansion

Word width may be increased simply by connecting the corresponding input control signals of multiple FIFOs. Status flags (EF, FF and HF) can be detected from any one FIFO. Figure 13 demonstrates an 18-bit word width by using the two FIFOs contained in the IDT72V81/72V82/72V83/72V84/72V85s. Any word width can be attained by adding FIFOs (Figure 13).

#### **Bidirectional Operation**

Applications which require data buffering between two systems (each system capable of Read and Write operations) can be achieved by pairing IDT72V81/72V82/72V83/72V84/72V85s as shown in Figure 16. Both Depth Expansion and Width Expansion may be used in this mode.

#### Data Flow-Through

Two types of flow-through modes are permitted, a read flow-through and write flow-through mode. For the read flow-through mode (Figure 17), the

FIFO permits a reading of a single word after writing one word of data into an empty FIFO. The data is enabled on the bus in (twEF + tA) ns after the rising edge of  $\overline{W}$ , called the first write edge, and it remains on the bus until the  $\overline{R}$  line is raised from low-to-high, after which the bus would go into a three-state mode after tRHZ ns. The  $\overline{EF}$  line would have a pulse showing temporary deassertion and then would be asserted.

In the write flow-through mode (Figure 18), the FIFO permits the writing of a single word of data immediately after reading one word of data from a full FIFO. The  $\overline{R}$  line causes the  $\overline{FF}$  to be deasserted but the  $\overline{W}$  line being low causes it to be asserted again in anticipation of a new data word. On the rising edge of  $\overline{W}$ , the new word is loaded in the FIFO. The  $\overline{W}$  line must be toggled when  $\overline{FF}$  is not asserted to write new data in the FIFO and to increment the write pointer.

#### **Compound Expansion**

The two expansion techniques described above can be applied together in a straightforward manner to achieve large FIFO arrays (see Figure 15).

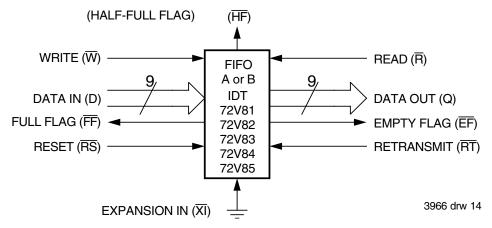


Figure 12. Block Diagram of One 512 x 9, 1,024 x 9, 2,048 x 9, 4,096 x 9 and 8,192 x 9 FIFO Used in Single Device Mode

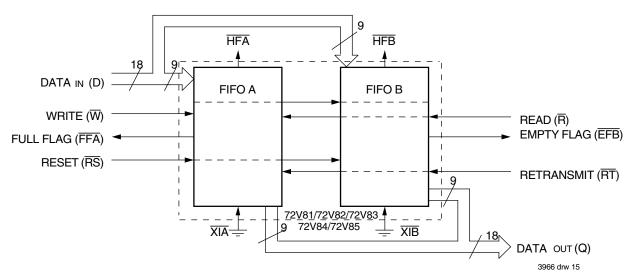


Figure 13. Block Diagram of One 512 x 18, 1,024 x 18, 2,048 x 18, 4,096 x 18 and 8,192 x 18 FIFO Memory Used in Width Expansion Mode

## TABLE I—RESET AND RETRANSMIT

Single Device Configuration/Width Expansion Mode

		Inputs Internal Status			Outputs			
Mode	RS	RT	Xī	Read Pointer	Write Pointer	ĒF	FF	HF
Reset	0	Х	0	Location Zero	Location Zero	0	1	1
Retransmit	1	0	0	Location Zero	Unchanged	Х	Х	Х
Read/Write	1	1	0	Increment <sup>(1)</sup>	Increment <sup>(1)</sup>	Х	Х	Х

NOTE:

1. Pointer will increment if flag is High.

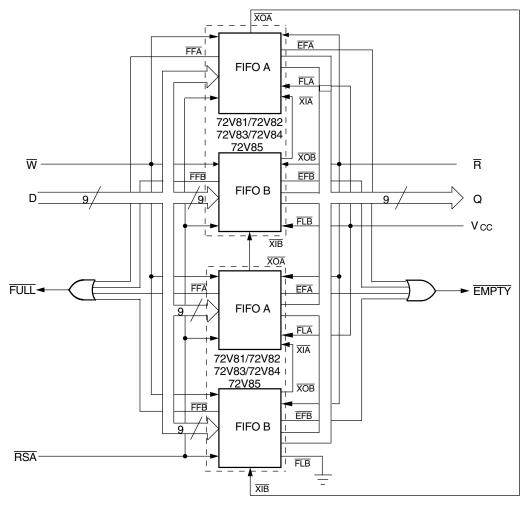
## TABLE II—RESET AND FIRST LOAD TRUTH TABLE

Depth Expansion/Compound Expansion Mode

	Inputs			Intern	al Status	Outputs	
Mode	RS	FL	Xī	Read Pointer	Write Pointer	ĒĒ	FF
Reset First Device	0	0	(1)	Location Zero	Location Zero	0	1
Reset All Other Devices	0	1	(1)	Location Zero	Location Zero	0	1
Read/Write	1	Х	(1)	Х	Х	Х	Х

NOTE:

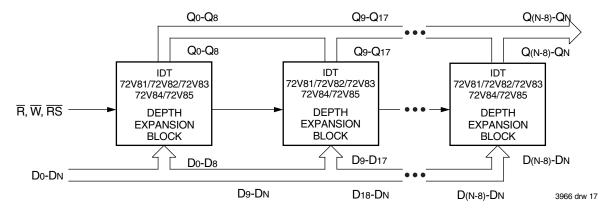
1. XI is connected to XO of previous device. See Figure 14. RS = Reset Input, FL/RT = First Load/Retransmit, EF = Empty Flag Output, FF = Full Flag Output, XI = Expansion Input, HF = Half-Full Flag Output



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Figure 14. Block Diagram of 2,048 x 9, 4,096 x 9, 8,192 x 9, 16,384 x 9 and 32,768 x 9 FIFO Memory (Depth Expansion)

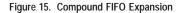
#### IDT72V81/72V82/72V83/72V84/72V853.3V CMOS DUAL ASYNCHRONOUS FIFO 512 x 9, 1024 x 9, 2048 x 9, 4096 x 9, 8192 x 9

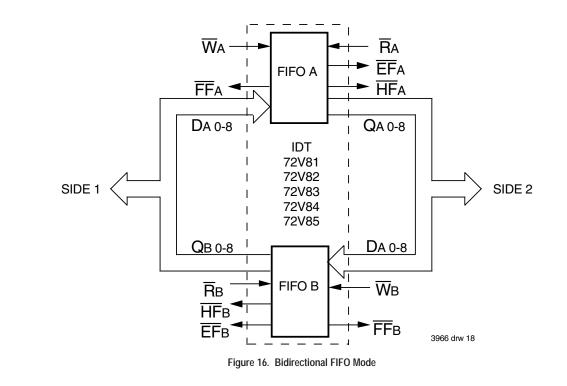


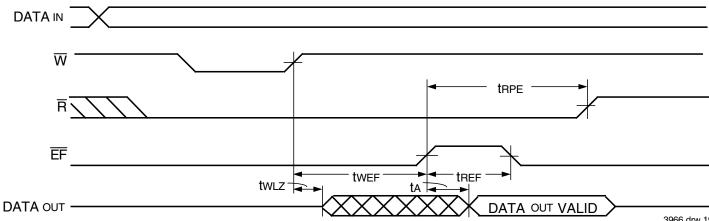
#### NOTES:

1. For depth expansion block see section on Depth Expansion and Figure 14.

2. For Flag detection see section on Width Expansion and Figure 13.



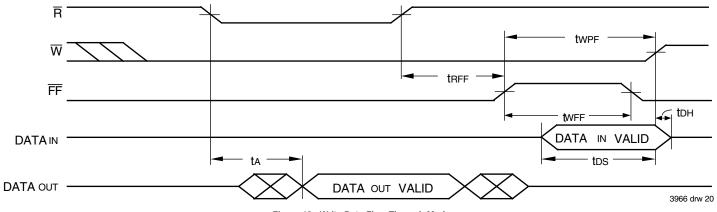






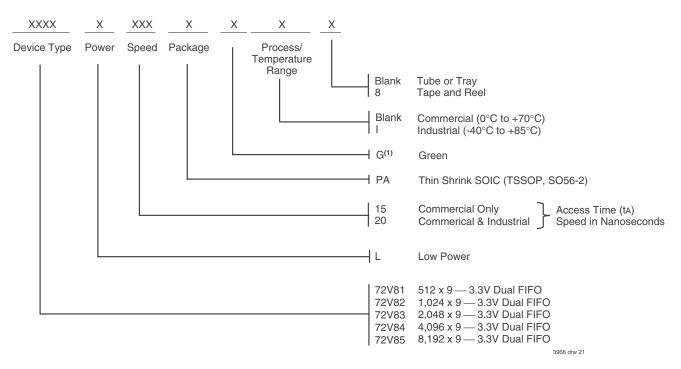
3966 drw 19







## ORDERING INFORMATION



#### NOTE:

LEAD FINISH (SnPb) parts are in EOL process. Product Discontinuation Notice - PDN# SP-17-02

<sup>1.</sup> Green parts are available. For specific speeds contact your local sales office.

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